WHAT IS CLAIMED IS:

1. A method of manufacturing an electric device comprising:

forming an amorphous semiconductor island over a first surface of a substrate;

crystallizing the amorphous semiconductor island by a thermal treatment to form a crystalline semiconductor island;

annealing the crystalline semiconductor island using a laser light:

forming a gate electrode adjacent to the crystalline semiconductor island with a gate insulating film interposed therebetween; and

introducing an impurity into the crystalline semiconductor island to form at least a source region, a drain region and a channel forming region between the source and drain regions,

wherein the step of annealing using a laser light comprises:

irradiating a laser light to the crystalline semiconductor island from a side of a first surface of the substrate,

reflecting a part of the laser light by a reflection plate being located adjacent to a second surface of the substrate, said second surface being opposed to the first surface of the substrate; and

irradiating the reflected laser light to the crystalline semiconductor island from a side of the second surface of the substrate.